

# FDMS2734

## N-Channel UltraFET Trench® MOSFET

250V, 14A, 122mΩ

### Features

- Max  $r_{DS(on)}$  = 122mΩ at  $V_{GS} = 10V$ ,  $I_D = 2.8A$
- Max  $r_{DS(on)}$  = 130mΩ at  $V_{GS} = 6V$ ,  $I_D = 1.7A$
- Low Miller Charge
- Optimized efficiency at high frequencies
- RoHS Compliant

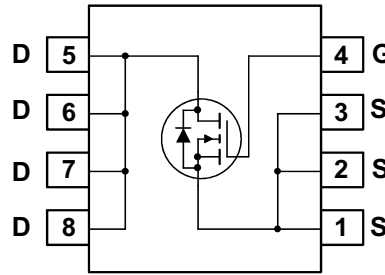
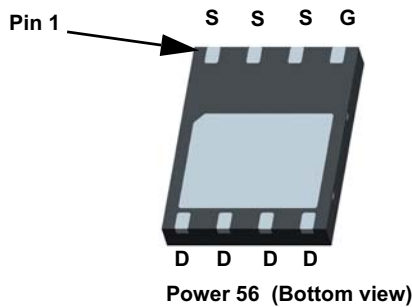


### General Description

UltraFET devices combine characteristics that enable benchmark efficiency in power conversion applications. Optimized for  $r_{DS(on)}$ , low ESR, low total and Miller gate charge, these devices are ideal for high frequency DC to DC converters.

### Application

- DC - DC Conversion



### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Rated Value	Units
$V_{DS}$	Drain to Source Voltage		250	V
$V_{GS}$	Gate to Source Voltage		±20	V
$I_D$	Drain Current -Continuous (Silicon limited)	$T_C = 25^\circ\text{C}$	14	A
	-Continuous	$T_A = 25^\circ\text{C}$ (Note 1a)	2.8	
	-Pulsed		30	
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	78	W
	Power Dissipation	$T_A = 25^\circ\text{C}$ (Note 1a)	2.5	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range		-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.6	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	50	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS2734	FDMS2734	Power 56	13"	12mm	3000 units

## Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	250			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		250		$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{V}$ ,			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			$\pm 100$	nA

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2	3	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-11		$\text{mV}/^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 2.8\text{A}$		105	122	m $\Omega$
		$V_{GS} = 6\text{V}, I_D = 1.7\text{A}$		110	130	
		$V_{GS} = 10\text{V}, I_D = 2.8\text{A}, T_J = 125^\circ\text{C}$		217	258	
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{V}, I_D = 2.8\text{A}$		11		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$		1775	2365	pF
$C_{oss}$	Output Capacitance			80	110	pF
$C_{rss}$	Reverse Transfer Capacitance			25	40	pF
$R_g$	Gate Resistance	$f = 1\text{MHz}$		0.9		$\Omega$

### Switching Characteristics

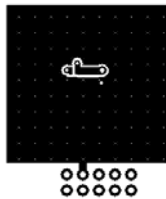
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 125\text{V}, I_D = 2.8\text{A}$ $V_{GS} = 10\text{V}, R_{GEN} = 6\Omega$		22	36	ns
$t_r$	Rise Time			10	20	ns
$t_{d(off)}$	Turn-Off Delay Time			36	58	ns
$t_f$	Fall Time			12	22	ns
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0\text{V to } 10\text{V}$	$V_{DD} = 125\text{V}$	30	42	nC
$Q_{gs}$	Gate to Source Gate Charge		$I_D = 2.8\text{A}$	7		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			9		nC

### Drain-Source Diode Characteristics

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 2.8\text{A}$ (Note 2)		0.75	1.20	V
$t_{rr}$	Reverse Recovery Time	$I_F = 2.8\text{A}, di/dt = 100\text{A}/\mu\text{s}$		79	119	ns
$Q_{rr}$	Reverse Recovery Charge			214	321	nC

#### Notes:

1:  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a.  $50^\circ\text{C}/\text{W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b.  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty cycle < 2.0%.

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

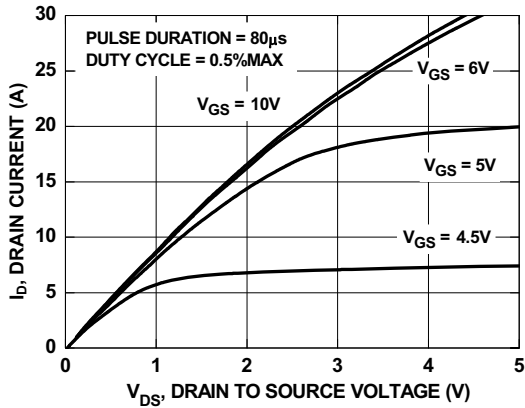


Figure 1. On Region Characteristics

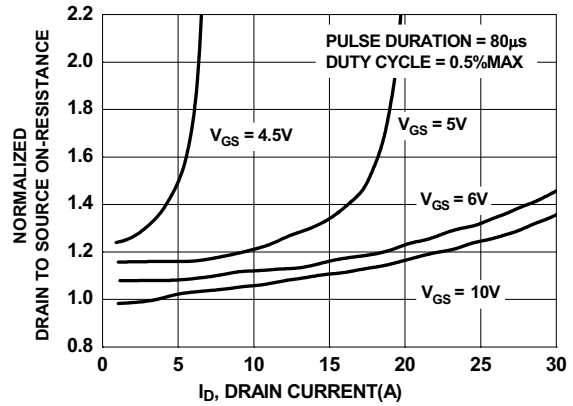


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

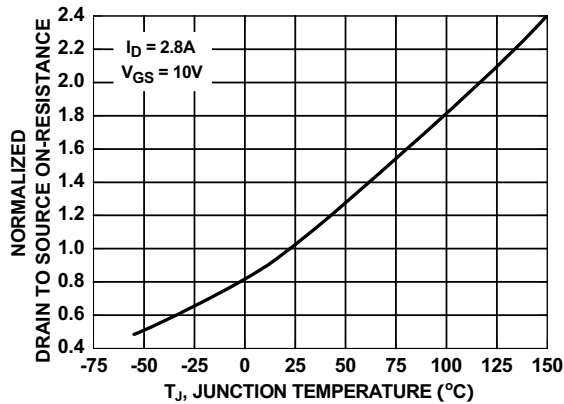


Figure 3. Normalized On Resistance vs Junction Temperature

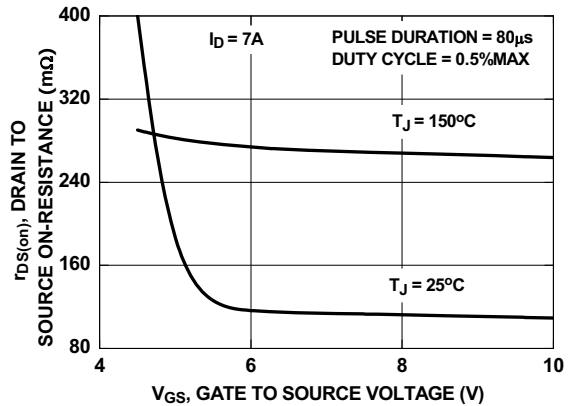


Figure 4. On-Resistance vs Gate to Source Voltage

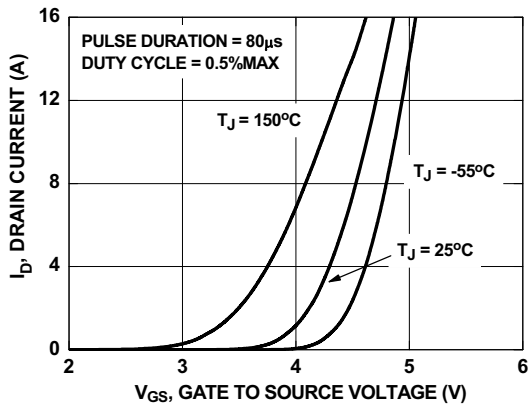


Figure 5. Transfer Characteristics

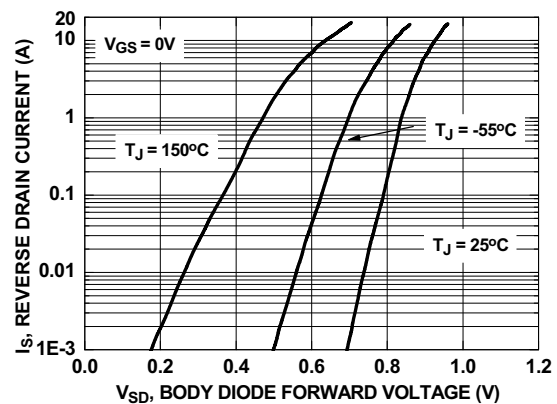
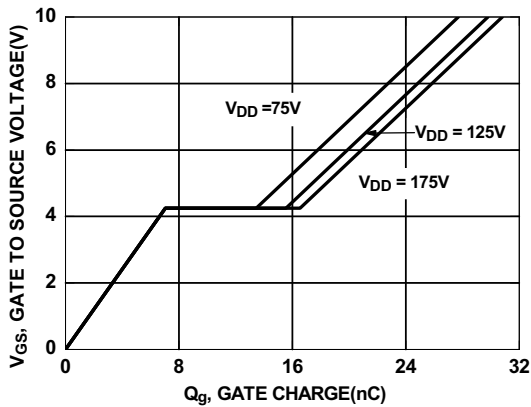
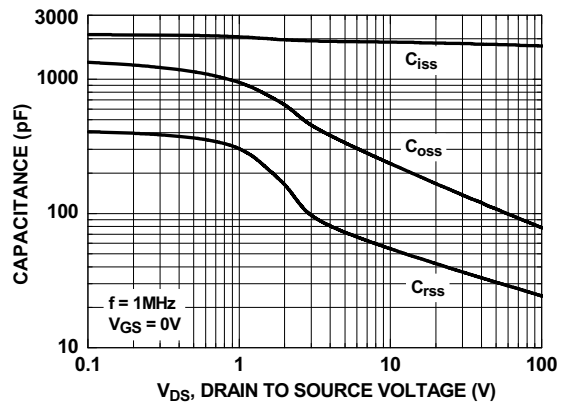


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

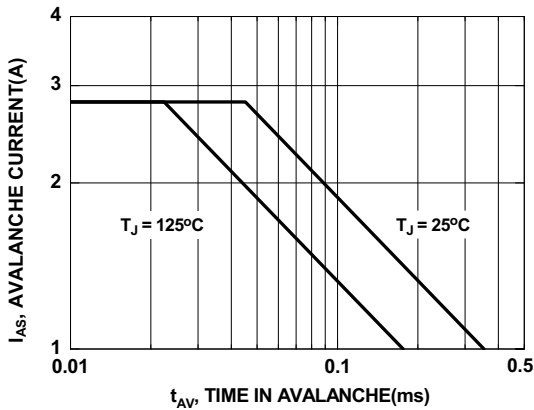
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



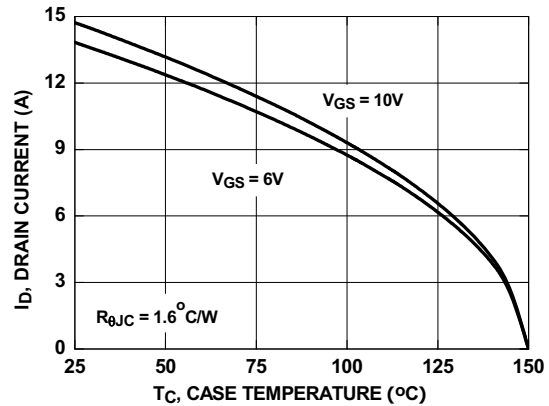
**Figure 7. Gate Charge Characteristics**



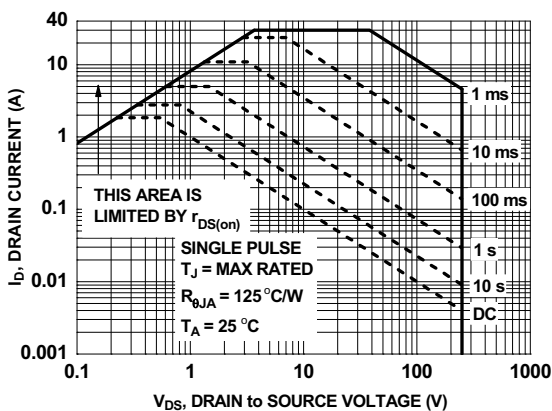
**Figure 8. Capacitance vs Drain to Source Voltage**



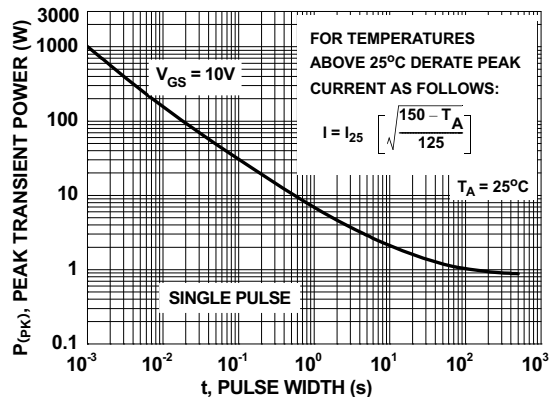
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs Case Temperature**

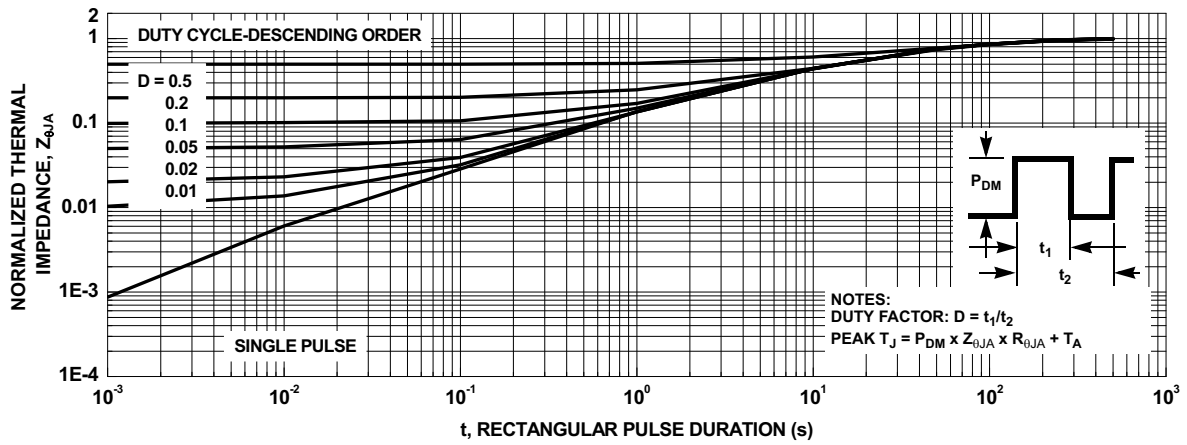


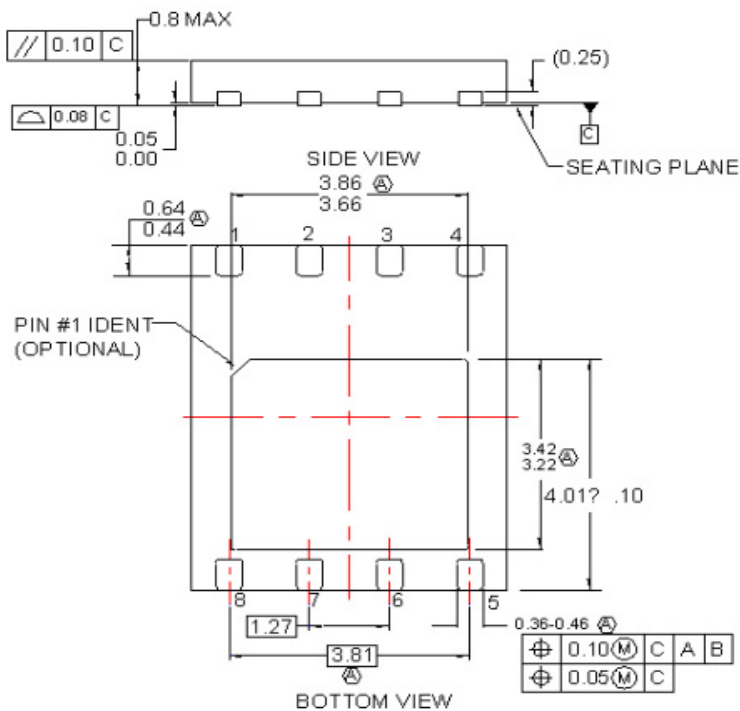
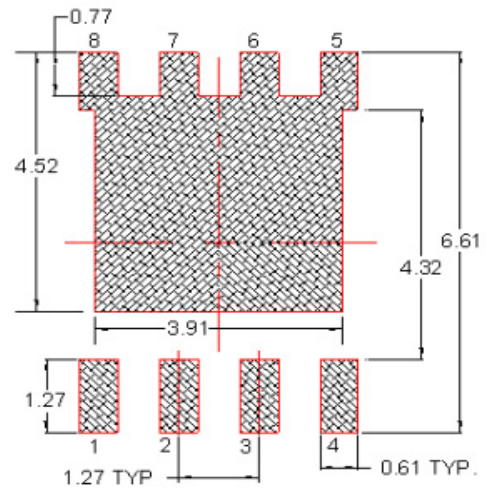
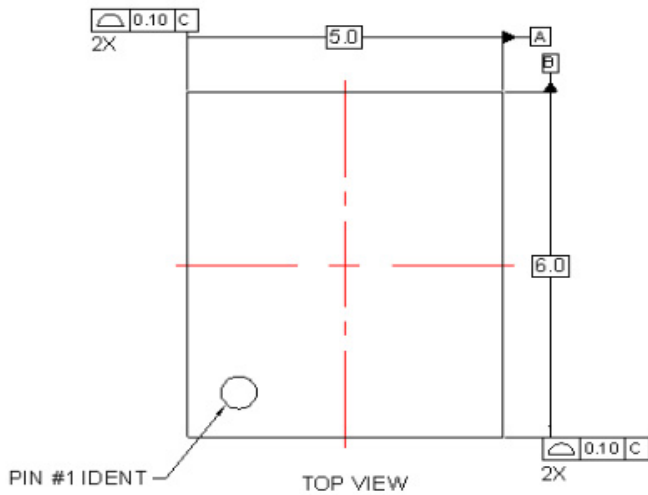
**Figure 11. Forward Bias Safe Operating Area**



**Figure 12. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted





**NOTES:**






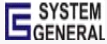
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- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
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